



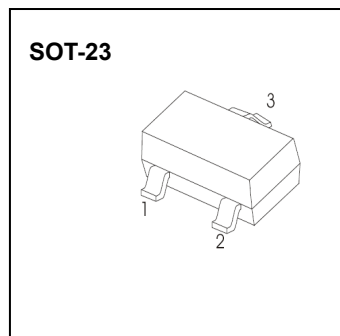
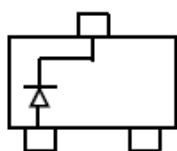
DONGGUAN NANJING ELECTRONICS LTD.,

SOT-23 Plastic-Encapsulate Diodes

BAS21/A/C/S SWITCHING DIODE

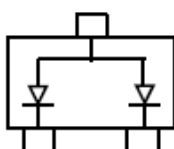
FEATURES

- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- For General Purpose Switching Applications
- High Conductance



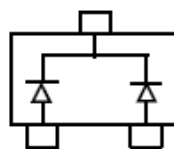
BAS21

Marking: JS



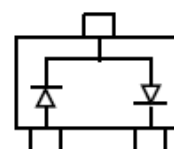
BAS21A

Marking:JS2



BAS21C

Marking:JS3



BAS21S

Marking: JS4

Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Repetitive peak reverse voltage	V_{RRM}	250	V
Working peak reverse voltage	V_{RWM}		
DC blocking voltage	V_R		
Forward continuous current	I_{FM}	400	mA
Average rectified output current	I_O	200	mA
Non-repetitive peak forward surge current @ t = 1.0μs	I_{FSM}	2.5	A
@ t = 1.0s		0.5	
Repetitive peak forward surge current	I_{FRM}	625	mA
Power dissipation	P_D	225	mW
Thermal resistance junction to ambient	$R_{\theta JA}$	55	°C/W
Junction temperature	T_J	150	°C
Storage temperature range	T_{STG}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu A$	250		V
Reverse voltage leakage current	I_R	$V_R = 200V$		0.1	μA
Forward voltage	V_F	$I_F = 100mA$ $I_F = 200mA$		1000 1250	mV
Diode capacitance	C_D	$V_R = 0V, f = 1MHz$		5	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 30mA, I_{rr} = 0.1 \times I_R, R_L = 100\Omega$		50	ns

Typical Characteristics

BAS21/A/C/S

